ON Semiconductor

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Non-Inverting 3-State Buffer

NL17SZ126

The NL17SZ126 is a single non-inverting buffer in tiny footprint packages.

Features

- Designed for 1.65 V to 5.5 V V_{CC} Operation
- 2.3 ns t_{PD} at $V_{CC} = 5 \text{ V (typ)}$
- Inputs/Outputs Overvoltage Tolerant up to 5.5 V
- I_{OFF} Supports Partial Power Down Protection
- Source/Sink 24 mA at 3.0 V
- Available in SC-88A, SC-74A, SOT-553, SOT-953 and UDFN6 Packages
- Chip Complexity < 100 FETs
- NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

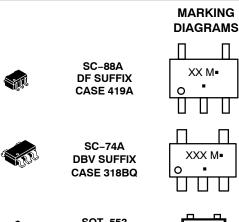


Figure 1. Logic Symbol



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SOT-553 XV5 SUFFIX CASE 463B





SOT-953 P5 SUFFIX CASE 527AE





UDFN6 1.45 x 1.0 CASE 517AQ





1

UDFN6 1.0 x 1.0 CASE 517BX



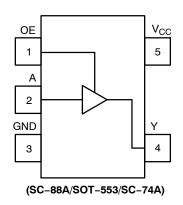
XX = Specific Device Code
M = Date Code*
= Pb-Free Package

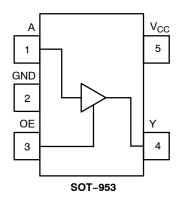
(Note: Microdot may be in either location)

*Date Code orientation and/or position may vary depending upon manufacturing location.

ORDERING INFORMATION

See detailed ordering, marking and shipping information in the package dimensions section on page 7 of this data sheet.





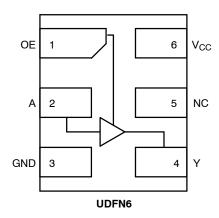


Figure 2. Pinout (Top View)

PIN ASSIGNMENT (SC-88A/SOT-553/SC-74A)

Pin	Function
1	OE
2	Α
3	GND
4	Υ
5	V _{CC}

PIN ASSIGNMENT (SOT-953)

Pin	Function
1	Α
2	GND
3	OE
4	Y
5	V _{CC}

PIN ASSIGNMENT (UDFN)

Pin	Function
1	OE
2	Α
3	GND
4	Υ
5	NC
6	V _{CC}

FUNCTION TABLE

Inp	Output	
OE	Α	Υ
Н	L	L
Н	Н	Н
L	Х	Z

X = Don't Care

MAXIMUM RATINGS

Symbol	Characteristics	3	Value	Unit
V _{CC}	DC Supply Voltage SC-74A, SC-88	SC-88A (NLV) A, SOT-953, SOT-553, UDFN6	-0.5 to +7.0 -0.5 to +6.5	V
V _{IN}	DC Input Voltage SC-74A, SC-88	SC-88A (NLV) A, SOT-953, SOT-553, UDFN6	-0.5 to +7.0 -0.5 to +6.5	V
V _{OUT}	SC-88A (NLV)	Active-Mode (High or Low State) Tri-State Mode (Note 1) Power-Down Mode (V _{CC} = 0 V)	-0.5 to V _{CC} + 0.5 -0.5 to +7.0 -0.5 to +7.0	V
	SC-74A, SC-88A, SOT-953, SOT-553, UDFN6	Active-Mode (High or Low State) Tri-State Mode (Note 1) Power-Down Mode (V _{CC} = 0 V)	-0.5 to V _{CC} + 0.5 -0.5 to +6.5 -0.5 to +6.5	V
I _{IK}	DC Input Diode Current	V _{IN} < GND	-50	mA
I _{OK}	DC Output Diode Current	V _{OUT} < GND	-50	mA
I _{OUT}	DC Output Source/Sink Current		±50	mA
I _{CC} or I _{GND}	DC Supply Current per Supply Pin or Ground Pi	±100	mA	
T _{STG}	Storage Temperature Range		-65 to +150	°C
TL	Lead Temperature, 1 mm from Case for 10 secs		260	°C
TJ	Junction Temperature Under Bias		+150	°C
$\theta_{ extsf{JA}}$	Thermal Resistance (Note 2)	SC-88A SC-74A SOT-553 SOT-953 UDFN6	377 320 324 254 154	°C/W
P _D	Power Dissipation in Still Air	SC-88A SC-74A SOT-553 SOT-953 UDFN6	332 390 386 491 812	mW
MSL	Moisture Sensitivity		Level 1	-
F _R	Flammability Rating	Oxygen Index: 28 to 34	UL 94 V-0 @ 0.125 in	-
V _{ESD}	ESD Withstand Voltage (Note 3)	Human Body Model Charged Device Model	2000 1000	V
I _{Latchup}	Latchup Performance (Note 4)		± 100	mA

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Applicable to devices with outputs that may be tri-stated.

2. Measured with minimum pad spacing on an FR4 board, using 10mm-by-1inch, 2 ounce copper trace no air flow per JESD51-7.

3. HBM tested to ANSI/ESDA/JEDEC JS-001-2017. CDM tested to EIA/JESD22-C101-F. JEDEC recommends that ESD qualification to EIA/JESD22-A115-A (Machine Model) be discontinued per JEDEC/JEP172A.

4. Tested to EIA/JESD78 Class II.

RECOMMENDED OPERATING CONDITIONS

Symbol	Characteristics		Min	Max	Unit
V _{CC}	Positive DC Supply Voltage		1.65	5.5	V
V _{IN}	DC Input Voltage		0	5.5	V
V _{OUT}		e-Mode (High or Low State) Tri-State Mode (Note 1) er-Down Mode (V _{CC} = 0 V)	0 0 0	V _{CC} 5.5 5.5	
T _A	Operating Temperature Range		-55	+125	°C
t _r , t _f	Input Rise and Fall Time SC-88A (NLV)	V _{CC} = 3.0 V to 3.6 V V _{CC} = 4.5 V to 5.5 V	0 0	100 20	ns/V
	Input Rise and Fall Time (SC-74A, SC-88A, SOT-953, SOT-553, UDFN6)	$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V} \\ V_{CC} = 2.3 \text{ V to } 2.7 \text{ V} \\ V_{CC} = 3.0 \text{ V to } 3.6 \text{ V} \\ V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	0 0 0	20 20 10 5	

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

DC ELECTRICAL CHARACTERISTICS

			V _{CC}	T,	T _A = 25°C		-55°C ≤ T	A ≤ 125°C	
Symbol	Parameter	Condition	(V)	Min	Тур	Max	Min	Max	Units
V _{IH}	High-Level Input		1.65 to 1.95	0.65 V _{CC}	-	_	0.65 V _{CC}	_	V
	Voltage		2.3 to 5.5	0.70 V _{CC}	-	-	0.70 V _{CC}	-	
V _{IL}	Low-Level Input		1.65 to 1.95	_	_	0.35 V _{CC}	-	0.35 V _{CC}	V
	Voltage		2.3 to 5.5	_	_	0.30 V _{CC}	-	0.30 V _{CC}	
V _{ОН}	High-Level Output Voltage	$\begin{split} V_{IN} &= V_{IH} \text{ or } V_{IL} \\ I_{OH} &= -100 \mu\text{A} \\ I_{OH} &= -4 \text{ mA} \\ I_{OH} &= -8 \text{ mA} \\ I_{OH} &= -12 \text{ mA} \\ I_{OH} &= -16 \text{ mA} \\ I_{OH} &= -24 \text{ mA} \\ I_{OH} &= -32 \text{ mA} \end{split}$	1.65 to 5.5 1.65 2.3 2.7 3.0 3.0 4.5	V _{CC} - 0.1 1.29 1.9 2.2 2.4 2.3 3.8	V _{CC} 1.4 2.1 2.4 2.7 2.5 4.0	- - - - -	V _{CC} - 0.1 1.29 1.9 2.2 2.4 2.3 3.8	- - - - -	>
V _{OL}	Low-Level Output Voltage	$\begin{split} &V_{IN} = V_{IH} \text{ or } V_{IL} \\ &I_{OL} = 100 \mu\text{A} \\ &I_{OL} = 4 \text{ mA} \\ &I_{OL} = 8 \text{ mA} \\ &I_{OL} = 12 \text{ mA} \\ &I_{OL} = 16 \text{ mA} \\ &I_{OL} = 24 \text{ mA} \\ &I_{OL} = 32 \text{ mA} \end{split}$	1.65 to 5.5 1.65 2.3 2.7 3.0 3.0 4.5	- - - - -	- 0.08 0.2 0.22 0.28 0.38 0.42	0.1 0.24 0.3 0.4 0.4 0.55 0.55	- - - - -	0.1 0.24 0.3 0.4 0.4 0.55 0.55	V
I _{IN}	Input Leakage Current	V _{IN} = 5.5 V or GND	1.65 to 5.5	_	-	±0.1	-	±1.0	μΑ
l _{OZ}	3-State Output Leakage Current	V _{OUT} = 0 V to 5.5 V	1.65 to 5.5	-	-	±0.5		±5.0	μΑ
I _{OFF}	Power Off Leakage Current	V _{IN} = 5.5 V or V _{OUT} = 5.5 V	0	-	_	1.0	-	10	μΑ
I _{CC}	Quiescent Supply Current	V _{IN} = V _{CC} or GND	5.5	-	-	1.0	-	10	μΑ

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

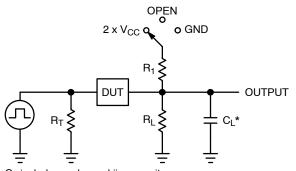
AC ELECTRICAL CHARACTERISTICS

			V _{CC}	T _A = 25°C		С	-55°C ≤ T	_Δ ≤ 125°C	
Symbol	Parameter	Condition	(V)	Min	Тур	Max	Min	Max	Units
t _{PLH,}	Propagation Delay, A to Y	R_L = 1 M Ω , C_L = 15 pF	1.65 to 1.95	-	6.0	10	=	10.5	ns
t _{PHL}	(Figures 3 and 4)	R_L = 1 M Ω , C_L = 15 pF	2.3 to 2.7	-	3.4	7.5	_	8.0	
		R_L = 1 M Ω , C_L = 15 pF	3.0 to 3.6	-	2.5	5.2	=	5.5	
		$R_L = 500 \Omega$, $C_L = 50 pF$		-	2.9	5.7	=	6.0	
		R_L = 1 M Ω , C_L = 15 pF	4.5 to 5.5	-	2.0	4.5	=	4.8	
		R_L = 500 Ω, C_L = 50 pF		_	2.3	5.0	=	5.3	
t _{PZH} ,	Output Enable Time,		1.65 to 1.95	-	6.5	9.5	=	10	ns
t _{PZL}	OE to Y (Figures 3 and 4)		2.3 to 2.7	-	3.6	8.5	=	9.0	
			3.0 to 3.6	-	2.8	6.2	=	6.5	
			4.5 to 5.5	-	2.0	5.5	=	5.8	
t _{PHZ} ,	Output Disable Time,		1.65 to 1.95	-	5.0	10	=	10.5	ns
t _{PLZ}	OE to Y (Figures 3 and 4)		2.3 to 2.7	-	3.3	8.0	=	8.5	
			3.0 to 3.6	-	2.7	5.7	=	6.0	
			4.5 to 5.5	-	2.6	4.7	_	5.0	

CAPACITIVE CHARACTERISTICS

Symbol	Parameter	Condition	Typical	Units
C _{IN}	Input Capacitance	V _{CC} = 5.5 V, V _{IN} = 0 V or V _{CC}	2.5	pF
C _{OUT}	Output Capacitance	$V_{CC} = 5.5 \text{ V}, V_{IN} = 0 \text{ V or } V_{CC}$	2.5	pF
C _{PD}	Power Dissipation Capacitance (Note 5)	10 MHz, V_{CC} = 3.3 V, V_{IN} = 0 V or V_{CC} 10 MHz, V_{CC} = 5.5 V, V_{IN} = 0 V or V_{CC}	9 11	pF

^{5.} C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: I_{CC(OPR)} = C_{PD} • V_{CC} • f_{in} + I_{CC}. C_{PD} is used to determine the no–load dynamic power consumption; P_D = C_{PD} • V_{CC}² • f_{in} + I_{CC} • V_{CC}.



Test	Switch Position	C _L , pF	R_L, Ω	R ₁ , Ω	
t _{PLH} / t _{PHL}	Open	See AC Characteristics Table			
t _{PLZ} / t _{PZL}	2 x V _{CC}	50	500	500	
t _{PHZ} / t _{PZH}	GND	50	500	500	

X = Don't Care

 C_L includes probe and jig capacitance R_T is Z_{OUT} of pulse generator (typically 50 $\Omega)$

f = 1 MHz

Figure 3. Test Circuit

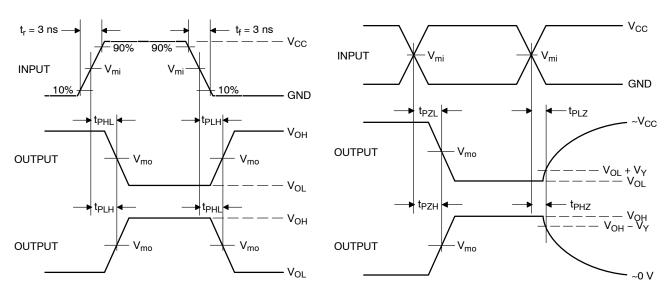


Figure 4. Switching Waveforms

		V _m		
V _{CC} , V	V _{mi} , V	t _{PLH} , t _{PHL}	t _{PZL} , t _{PLZ} , t _{PZH} , t _{PHZ}	V _Y , V
1.65 to 1.95	V _{CC} /2	V _{CC} /2	V _{CC} /2	0.15
2.3 to 2.7	V _{CC} /2	V _{CC} /2	V _{CC} /2	0.15
3.0 to 3.6	V _{CC} /2	V _{CC} /2	V _{CC} /2	0.3
4.5 to 5.5	V _{CC} /2	V _{CC} /2	V _{CC} /2	0.3

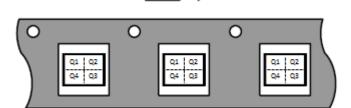
DEVICE ORDERING INFORMATION

Device	Packages	Specific Device Code	Pin 1 Orientation (See below)	Shipping [†]
NL17SZ126DFT2G	SC-88A	M2	Q4	3000 / Tape & Reel
NLV17SZ126DFT2G*	SC-88A	M2	Q4	3000 / Tape & Reel
NL17SZ126DBVT1G	SC-74A	AJ	Q4	3000 / Tape & Reel
NL17SZ126XV5T2G	SOT-553	M2	Q4	4000 / Tape & Reel
NL17SZ126P5T5G	SOT-953	R (Rotated 180° CW)	Q2	8000 / Tape & Reel
NL17SZ126MU1TCG (In Development)	UDFN6, 1.45 x 1.0, 0.5P	TBD	Q4	3000 / Tape & Reel
NL17SZ126MU3TCG (In Development)	UDFN6, 1.0 x 1.0, 0.35P	TBD	Q4	3000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

Pin 1 Orientation in Tape and Reel

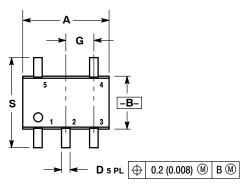
Direction of Feed

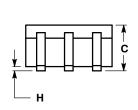


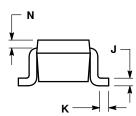
^{*}NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable.

PACKAGE DIMENSIONS

SC-88A (SC-70-5/SOT-353) CASE 419A-02 ISSUE L



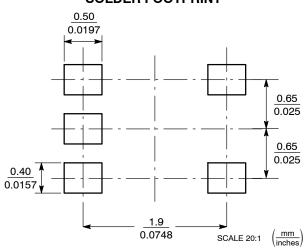




- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
 3. 419A-01 OBSOLETE. NEW STANDARD 419A-02.
 4. DIMENSIONS A AND B DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	INCHES		MILLIMETERS		
DIM	MIN	MAX	MIN	MAX	
Α	0.071	0.087	1.80	2.20	
В	0.045	0.053	1.15	1.35	
С	0.031	0.043	0.80	1.10	
D	0.004	0.012	0.10	0.30	
G	0.026 BSC		0.65 BSC		
Н		0.004		0.10	
J	0.004	0.010	0.10	0.25	
K	0.004	0.012	0.10	0.30	
N	0.008 REF		0.20 REF		
S	0.079	0.087	2.00	2.20	

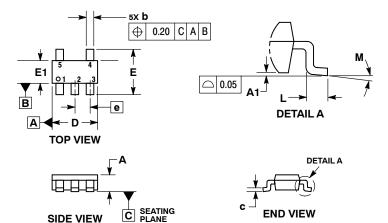
SOLDER FOOTPRINT*



^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PACKAGE DIMENSIONS

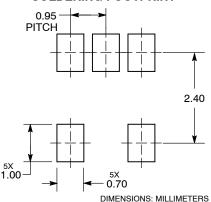
SC-74A CASE 318BQ **ISSUE B**



- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
 2. CONTROLLING DIMENSION: MILLIMETERS.
 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
 4. DIMENSIONS A AND B DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.15 PER SIDE.

	MILLIMETERS		
DIM	MIN	MAX	
Α	0.90	1.10	
A1	0.01	0.10	
b	0.25	0.50	
С	0.10	0.26	
D	2.85	3.15	
E	2.50	3.00	
E1	1.35	1.65	
е	0.95 BSC		
Ĺ	0.20 0.60		
М	0° 10°		

RECOMMENDED SOLDERING FOOTPRINT*

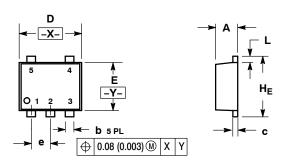


*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PACKAGE DIMENSIONS

SOT-553, 5 LEAD

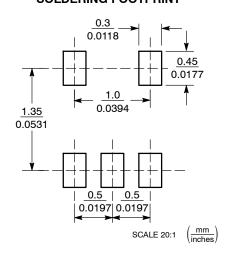
CASE 463B ISSUE C



- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: MILLIMETERS
 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH
 THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM
 THICKNESS OF BASE MATERIAL.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.50	0.55	0.60	0.020	0.022	0.024
b	0.17	0.22	0.27	0.007	0.009	0.011
С	0.08	0.13	0.18	0.003	0.005	0.007
D	1.55	1.60	1.65	0.061	0.063	0.065
E	1.15	1.20	1.25	0.045	0.047	0.049
е		0.50 BSC			0.020 BSC	
L	0.10	0.20	0.30	0.004	0.008	0.012
HE	1.55	1.60	1.65	0.061	0.063	0.065

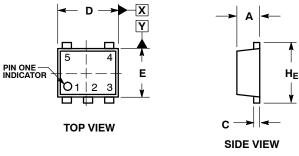
SOLDERING FOOTPRINT*

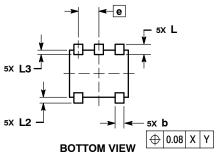


*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PACKAGE DIMENSIONS

SOT-953 CASE 527AE ISSUE E





- NOTES:

 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.

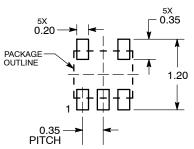
 2. CONTROLLING DIMENSION: MILLIMETERS

 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.

 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	MILLIMETERS			
DIM	MIN	NOM	MAX	
Α	0.34	0.37	0.40	
b	0.10	0.15	0.20	
С	0.07	0.12	0.17	
D	0.95	1.00	1.05	
E	0.75	0.80	0.85	
е	0.35 BSC			
HE	0.95	1.00	1.05	
L	0.175 REF			
L2	0.05	0.10	0.15	
L3			0.15	

SOLDERING FOOTPRINT*

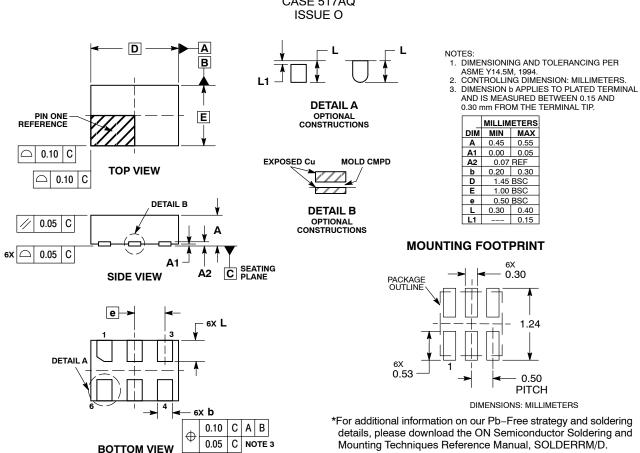


DIMENSIONS: MILLIMETERS

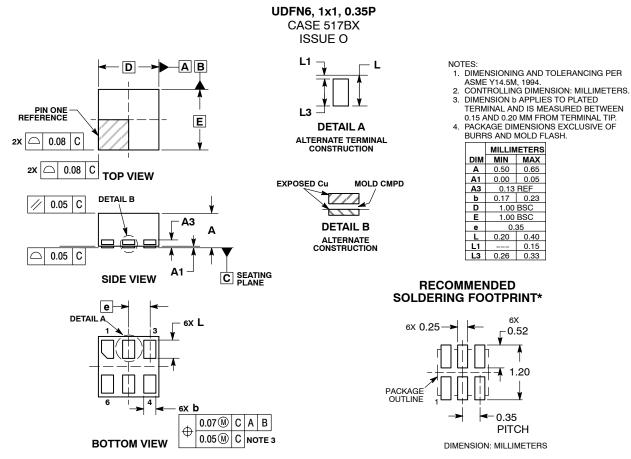
^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PACKAGE DIMENSIONS

UDFN6, 1.45x1.0, 0.5P CASE 517AQ **ISSUE O**



PACKAGE DIMENSIONS



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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